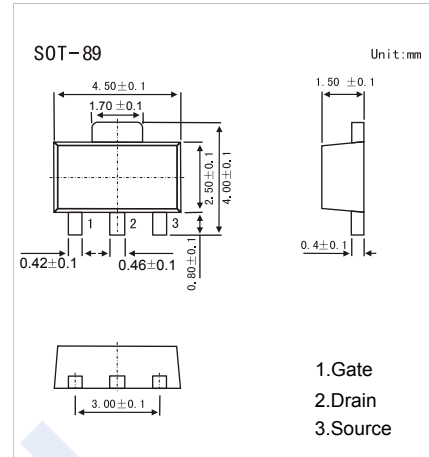
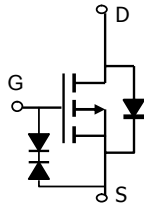


P-Channel MOSFET

2SJ360

■ Features

- $V_{DS} (V) \approx -60V$
- $I_D \approx -1 A$
- $R_{DS(ON)} < 0.73 \Omega$ ($V_{GS} \approx -10V$)
- $R_{DS(ON)} < 1.2 \Omega$ ($V_{GS} \approx -4V$)
- High forward transfer admittance



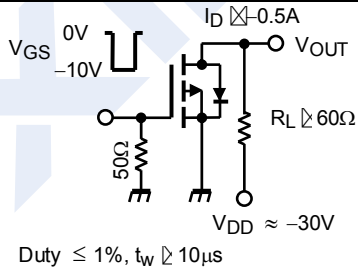
■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-60	V
Drain-Gate voltage ($R_{GS} = 20 k \Omega$)	V_{DG}	-60	
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current	I_D	-1	A
Pulsed Drain Current	I_{DM}	-4	
Power Dissipation	P_D	0.5	W
		1.5	
Thermal Resistance, Channel to Ambient	$R_{\theta JA}$	250	$^\circ C/W$
Junction Temperature	T_J	150	$^\circ C$
Junction Storage Temperature Range	T_{stg}	-55 to 150	

P-Channel MOSFET

2SJ360

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DS}	$I_D = -10\text{mA}$, $V_{GS} = 0\text{V}$	-60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60\text{V}$, $V_{GS} = 0\text{V}$			-100	μA
Gate-Body leakage current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 16\text{V}$			± 10	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = -10\text{V}$, $I_D = -1\text{mA}$	-0.8		-2	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4\text{V}$, $I_D = -0.5\text{A}$			1.2	Ω
		$V_{GS} = -10\text{V}$, $I_D = -0.5\text{A}$			0.73	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{V}$, $I_D = -0.5\text{A}$	0.5	1		S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = -10\text{V}$, $f = 1\text{MHz}$		155		pF
Output Capacitance	C_{oss}			22		
Reverse Transfer Capacitance	C_{rss}			75		
Total Gate Charge	Q_g	$V_{GS} = -10\text{V}$, $V_{DS} = -48\text{V}$, $I_D = -1\text{A}$		6.5		nC
Gate Source Charge	Q_{gs}			4.5		
Gate Drain Charge	Q_{gd}			2		
Turn-On DelayTime	$t_{d(on)}$	 $I_D \approx -0.5\text{A}$ V_{GS} 0V, -10V $V_{DD} \approx -30\text{V}$ $R_L \geq 60\Omega$ $\text{Duty} \leq 1\%$, $t_w \geq 10\mu\text{s}$		20		ns
Turn-On Rise Time	t_r			17		
Turn-Off DelayTime	$t_{d(off)}$			100		
Turn-Off Fall Time	t_f			20		
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1\text{A}$, $V_{GS} = 0$, $dI/dt = 50\text{A}/\mu\text{s}$		50		nC
Body Diode Reverse Recovery Charge	Q_{rr}			45		
Continuous drain reverse current	I_{DR}				-1	A
Pulse drain reverse current	I_{DRP}				-4	
Diode Forward Voltage	V_{SD}	$I_{DR} = -1\text{A}$, $V_{GS} = 0\text{V}$			-1.8	V

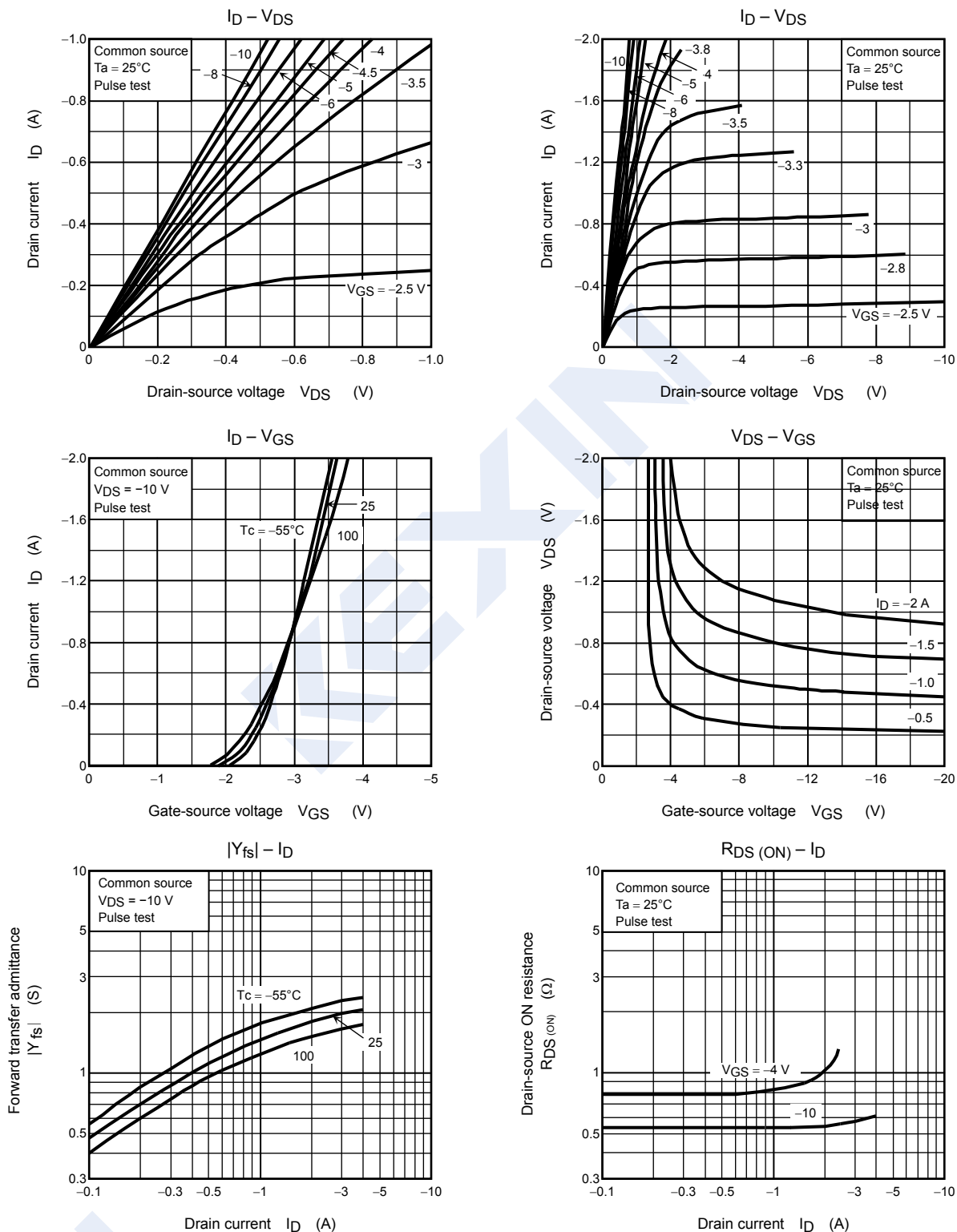
■ Marking

Marking	Z*8
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P-Channel MOSFET

2SJ360

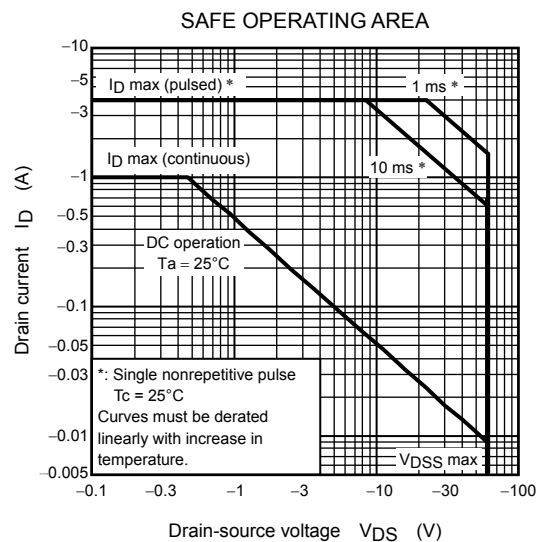
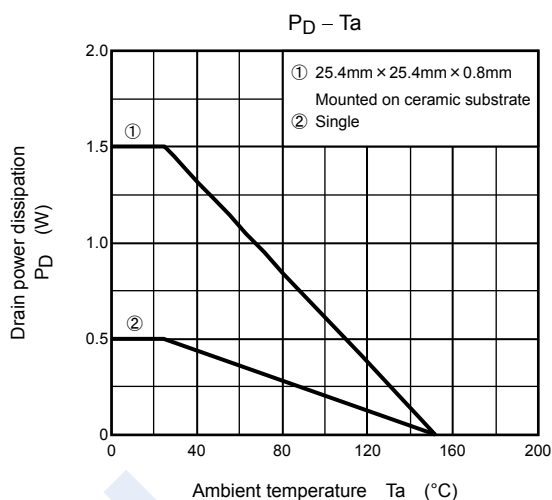
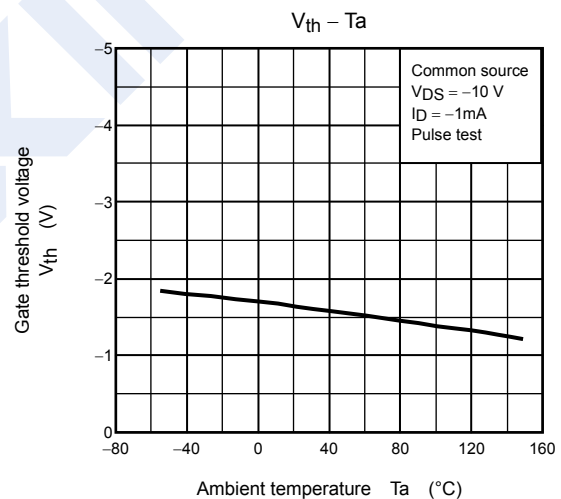
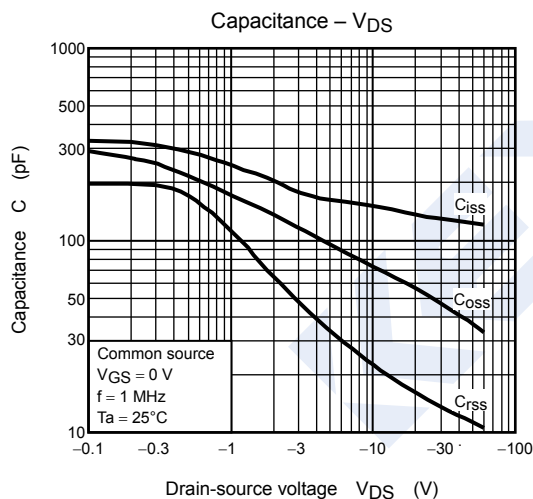
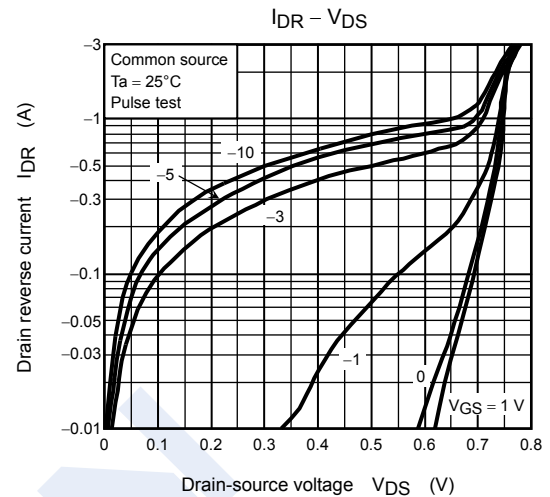
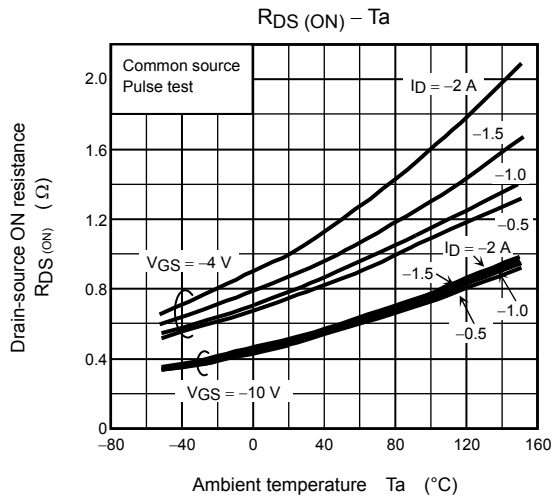
■ Typical Characteristics



P-Channel MOSFET

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Typical Characteristics



P-Channel MOSFET

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■ Typical Characteristics

